JSMICRO SEMICONDUCTOR

BT258U-600R

GENERAL DESCRIPTION

Passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

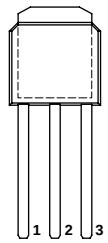
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT258U-	**500R**	**600R**	**800R**	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages	500	600	800	V
$I_{T(AV)}$	Average on-state current	5	5	5	A
$I_{T(RMS)}$	RMS on-state current	8	8	8	A
I_{TSM}	Non-repetitive peak on-state current	75	75	75	A

PINNING - TO251

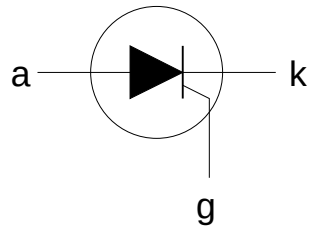
PIN NUMBER	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

PIN CONFIGURATION



Top view MBK915

SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500R	**-600R**	**-800R**	
V_{DRM}, V_{RRM}	Repetitive peak off-state voltages		-	500[1]	600[1]	800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 111$ ˚C	-	5			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	8			A
I_{TSM}	Non-repetitive peak on-state current	half sine wave; T_j = 25 ˚C prior to surge					
		t = 10 ms	-	75			A
		t = 8.3 ms	-	82			A
I^2t	I^2t for fusing	t = 10 ms	-	28			A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	I_{TM} = 10 A; I_G = 50 mA; dI_G/dt = 50 mA/µs	-	50			A/µs
I_{GM}	Peak gate current		-	2			A
V_{GM}	Peak gate voltage		-	5			V
V_{RGM}	Peak reverse gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			˚C
T_j	Operating junction temperature		-	125[2]			˚C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

2 Note: Operation above 110˚C may require the use of a gate to cathode resistor of 1kΩ or less.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	2.0	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	70	-	K/W

STATIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	V_D = 12 V; I_T = 0.1 A	-	50	200	µA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A	-	0.4	10	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A	-	0.3	6	mA
V_T	On-state voltage	I_T = 16 A	-	1.3	1.5	V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.4	1.5	V
		V_D = $V_{DRM(max)}$; I_T = 0.1 A; T_j = 110 ˚C	0.1	0.2	-	V
I_D, I_R	Off-state leakage current	V_D = $V_{DRM(max)}$; V_R = $V_{RRM(max)}$; T_j = 125 ˚C	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 ˚C; exponential waveform; R_{GK} = 100 Ω	50	100	-	V/µs
t_{gt}	Gate controlled turn-on time	I_{TM} = 10 A; V_D = $V_{DRM(max)}$; I_G = 5 mA; dI_G/dt = 0.2 A/µs	-	2	-	µs
t_q	Circuit commutated turn-off time	V_D = 67% $V_{DRM(max)}$; T_j = 125 ˚C; I_{TM} = 12 A; V_R = 24 V; dI_{TM}/dt = 10 A/µs; dV_D/dt = 2 V/µs; R_{GK} = 1 kΩ	-	100	-	µs

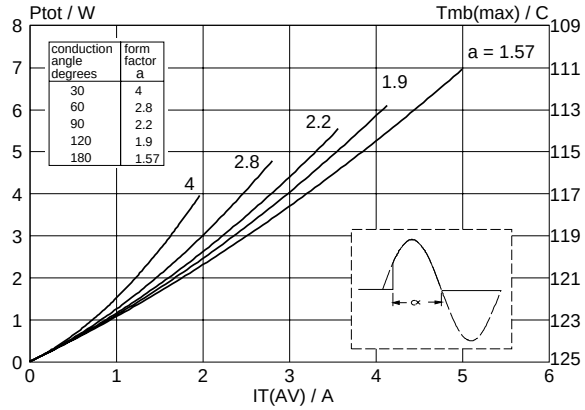


Fig.1. Maximum on-state dissipation, P_{tot}, versus average on-state current, $I_{T(AV)}$, where a = form factor = $I_{T(RMS)}$/ $I_{T(AV)}$.

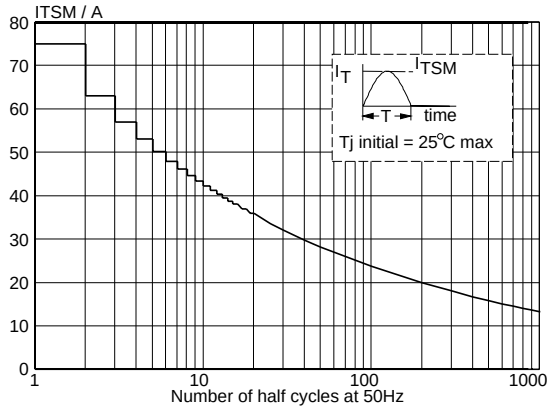


Fig.4. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus number of cycles, for sinusoidal currents, f = 50 Hz.

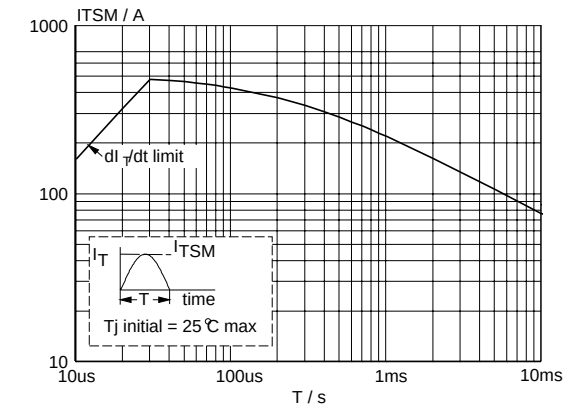


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM}, versus pulse width t_p, for sinusoidal currents, $t_p \leq 10ms$.

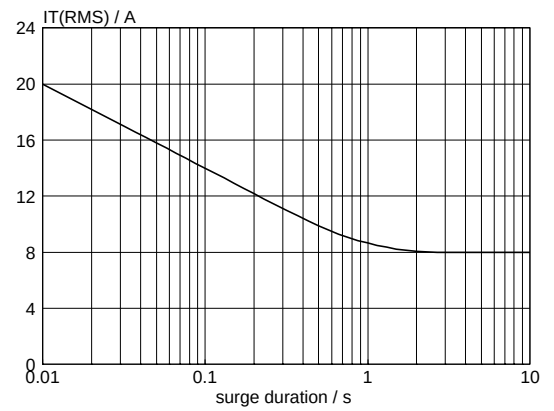


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \leq 111^{\circ}C$.

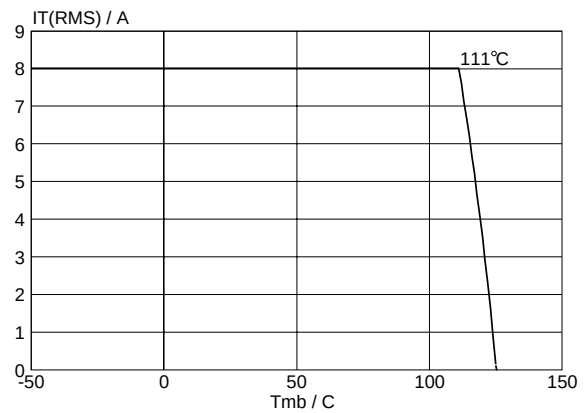


Fig.3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb}.

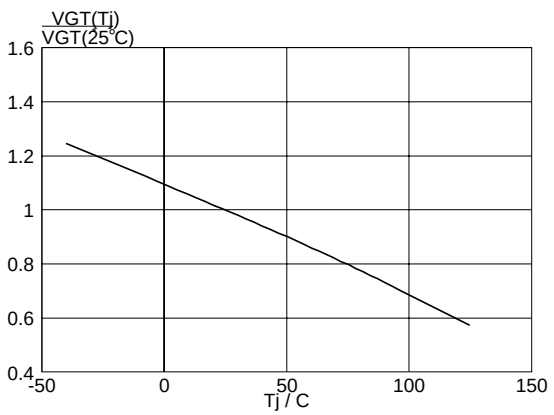


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)$/ $V_{GT}(25^{\circ}C)$, versus junction temperature T_j.

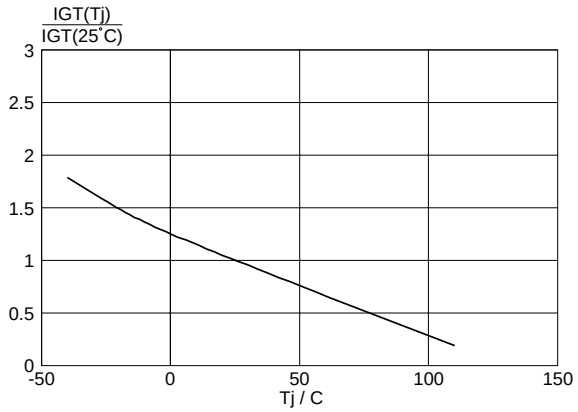


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/ I_{GT}(25^{\circ}C)$, versus junction temperature T_j.

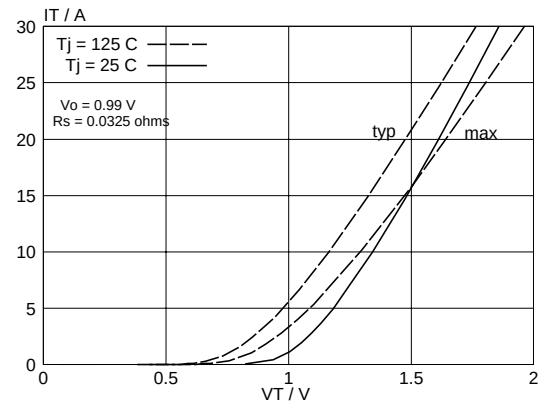


Fig.10. Typical and maximum on-state characteristic.

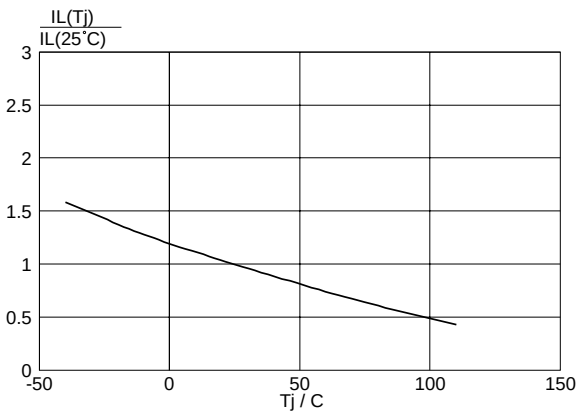


Fig.8. Normalised latching current $I_L(T_j)/ I_L(25^{\circ}C)$, versus junction temperature T_j.

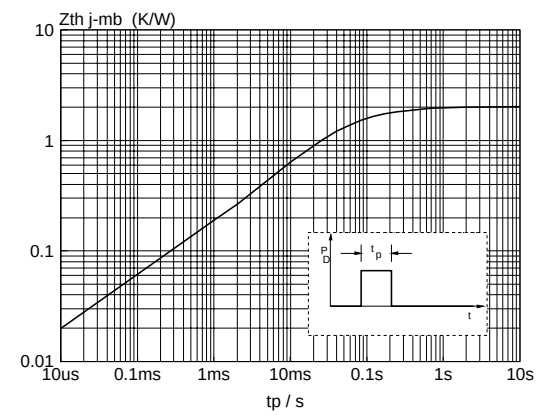


Fig.11. Transient thermal impedance $Z_{th\ j\text{-}mb}$, versus pulse width t_p.

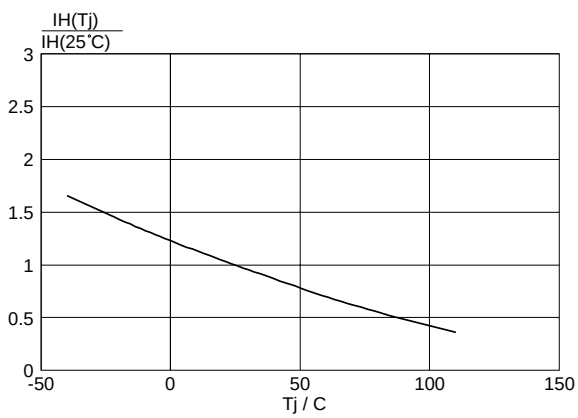


Fig.9. Normalised holding current $I_H(T_j)/ I_H(25^{\circ}C)$, versus junction temperature T_j.

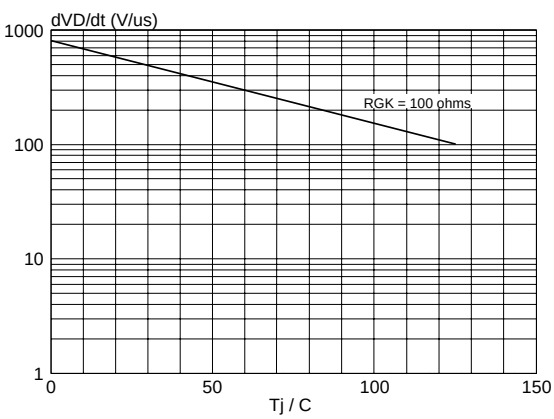
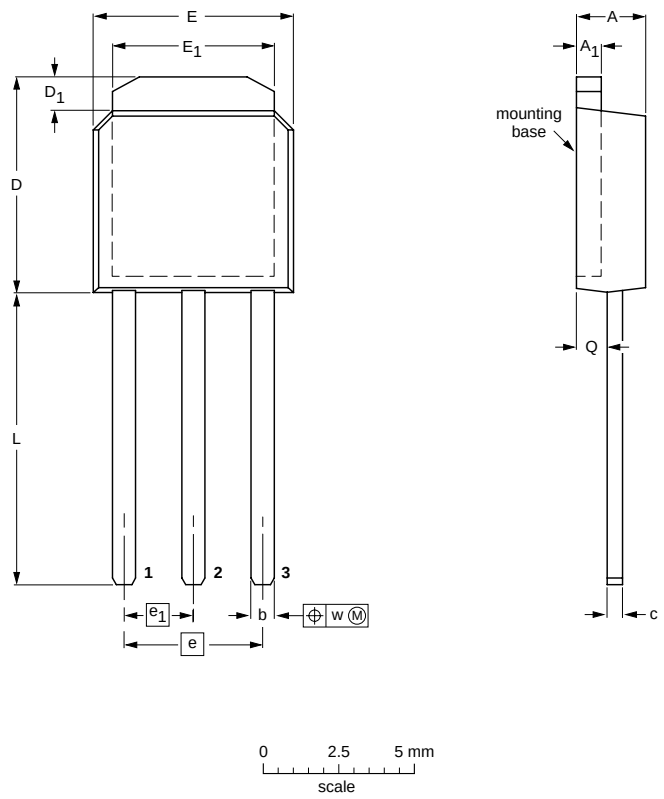


Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j.

MECHANICAL DATA

Dimensions in mm Net Mass: 1.3 g

Plastic single-ended package (Philips version of I-PAK); 3 leads (in-line) **TO251**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D	D_1	E	E_1	e	e_1	L	Q
mm	2.38 2.22	0.89 0.71	0.89 0.71	0.56 0.46	7.28 6.94	1.06 0.96	6.73 6.47	5.36 5.26	4.57	2.285	9.8 9.4	1.00 1.10

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT533		TO-251				99-02-18

Fig.13. SOT533 (TO251). pin 2 connected to mounting base.